

AMENDMENTS TO THE CLAIMS:

Claim 1. (Currently amended) A method of forming a dielectric chamber in the vicinity of a semiconductor device area, the method comprising:

forming a dummy structure over a semiconductor substrate;

depositing a dielectric layer over the dummy structure;

forming an opening through the dielectric layer to the dummy structure; and

removing the dummy structure to form the dielectric chamber, wherein forming the dummy structure comprises forming the dummy structure using a polysilicon material.

Claim 2. (Original) The method of claim 1, further comprising filling the dielectric chamber with a gas.

Claim 3. (Original) The method of claim 2, wherein the gas comprises air.

Claim 4. (Original) The method of claim 2, wherein the gas comprises an inert gas.

Claim 5. (Canceled).

Claim 6. (Original) The method of claim 1, wherein removing the dummy structure comprises using a downstream plasma etching process.

Claim 7. (Original) The method of claim 1, further comprising depositing a dielectric layer over the semiconductor substrate before forming the dummy structure.

Claim 8. (Original) The method of claim 1, further comprising depositing an oxide layer over the dummy structure.

Claim 9. (Original) The method of claim 8, wherein the hole extends through the oxide layer to the dummy structure.

Claim 10. (Original) The method of claim 8, further comprising forming a metal liner over the oxide layer.

Claim 11. (Currently amended) A method of forming a dielectric chamber in the vicinity of a semiconductor device area, the method comprising:

forming a dummy structure over a semiconductor substrate;

depositing a dielectric layer over the dummy structure;

forming an opening through the dielectric layer to the dummy structure;

removing the dummy structure to form the dielectric chamber; and ~~The method of claim 1, further comprising~~ depositing a metal layer over the dummy structure.

Claim 12. (Original) The method of claim 11, further comprising polishing the metal layer.

Claim 13. (Original) The method of claim 1, further comprising depositing an insulating material over the dielectric layer.

Claim 14. (Original) The method of claim 13, further comprising depositing another dielectric layer over the insulating material.

Claim 15. (Original) The method of claim 14, wherein the hole is formed through the another dielectric layer, the insulating layer, and the dielectric layer.

Claim 16. (Currently amended) The method of claim 11 †, further comprising:
~~depositing a metal layer over the dummy structure;~~
polishing the metal layer;
depositing an insulating material over the metal layer; and
forming a contact stud through the insulating layer and the dielectric layer so that the contact stud contacts the metal layer.

Claim 17. (Original) The method of claim 1, wherein said dielectric chamber is formed in one of the active layer, the passive layer, and the first metal layer.

Claim 18. (Original) The method of claim 1, wherein the dummy structure is formed in multiple levels among conductive lines.

Claim 19. (Original) The method of claim 18, wherein the conductive lines comprise a first set of conductive lines at a first level and a second set of conductive lines at a second level over the first level.

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Claim 20. (Original) The method of claim 19, wherein the second set of conductive lines cross the first set of conductive lines.

Claims 21-47. (Canceled).